PCN Number: 2			0160802000				PCN I	Date:	08/03/2016		
Title:	Wafer Diame	er (Cha	ang	e for Select D	EF-EP Niche Dev	ices	in LBC	3S Proc	ess at DL-LIN	
Custome	er Contact:		PC	IN N	<u>Manager</u>		De	pt:	Quality	Services	
Proposed 1 st Ship Date:			01/03/2017 Estim			Estimated Sam Availability:	ıple	ple Date provided at sample request.			
Change [•]	Гуре:										
Asse	mbly Site		[Assembly Process			Assembly Materials			
Desi	gn				Electrical Sp	ecification		Mechanical Specification			
Test	Site				Packing/Shipping/Labeling			Test	Process	5	
Wafe	er Bump Site				Wafer Bump	Material		Waf	er Bump	Process	
Wafer Fab Site					Wafer Fab M	laterials		Waf	er Fab P	rocess	
			[Part number change						
PCN Details											

Description of Change:

This change notification is to announce a wafer diameter change for select DEF-EP Niche Devices in LBC3S Process at DL-LIN.

Current	New
Site/Process/Wafer Diameter	Site/Process/Wafer Diameter
DL-LIN/LBC3S Process/150mm	DL-LIN/LBC3S Process/200mm

The LBC3S process technology/200mm wafer was previously qualified at DL-LIN and has been running successfully since 2000.

Reason for Change:

Continuity of supply.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

Changes to product identification resulting from this PCN:

Note: This is <u>not a fab site change</u>. No change to the Chip Site Location.

Current

Chip Site	Chip site code (20L)	Chip country code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas

Sample Product Shipping Label (not actual product label)

TEXAS INSTRUMENTS ADE IN: Malaysia 2DC: 2Q: MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: 39 LBL: 5A (L)T0:1750		(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (P) (2P) REV: (V) 0033317 (20L) CS0: SHE (21L) CC0:USA (22L) AS0: MLA (23L) AC0: MYS	
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Reference Qualification: LBC3s Process at DFAB

Qualification Data: (Approved: 2000)								
This qualification has been developed for the validation of this change. The								
qualification data will validate that the proposed change meets the applicable released								
technical specifications.								
Wafor Fab Sito:	Wafar Eab Cita: DEAR Wafar Diamatari 200mm							
Wafer Fab Process:								
Qualification:	Plan	🛛 Te	st Results					
			Stresuits	Samn	la Siza /	Fail		
Reliability Test		Con	ditions					
**I ife Test		155	C (240hrs)	116/0	116/0	116/0		
**Biased HAST		1300	C/85%RH (96 Hrs)	77/0	77/0	77/0		
**Thermal Shock		-65/	(+150C (1000 Cycles)	77/0	77/0	77/0		
ESD HBM		2.5	(V	3/0	3/0	3/0		
Electrical Characterization				Pass	Pass	Pass		
Bond Strength				76/0	76/0	76/0		
Die Shear				5/0	5/0	5/0		
Manufacturability (Wafer Fab)			site spec	Approved	-	-		
Manufacturability (Ass	embly)	(per	mfg. Site specification)	Approved	-	-		
**Preconditioning	: Level 3	-235	С					
	1	Qua	al Vehicle 2: SN75976A2DL					
Wafer Fab Site:	DFAB		Wafer Diameter: 200mm					
Wafer Fab Process:	LBC3s							
Qualification:] Plan	<u> </u> Те	st Results					
Reliability Test		Cor	nditions	Samp	le Size /	Fail		
		4 5		Lot 1	Lot2	Lot 3		
**Life Test		15	5C (240hrs)	116/0	116/0	116/0		
ESD HBM		2.5	KV	3/0	3/0	3/0		
ESD CDM			KV	3/0	3/0	3/0		
Electrical Characterization				Pass	Pass	Pass		
Latch-Up				5/0	5/0	5/0		
Manufacturability (Wal	rer Fab)	Per	site spec	Approved	-	-		
Manufacturability (Ass	embly)	(pe	r mrg. Site specification)	Approved	-	-		
**Preconditioning	j: Level 3	-220						

Qualification Results (2000 and 2002)

Automotive Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

Supplier Name:	Texas Instruments Inc.	Supplier Wafer Fabrication Site:	Texas Instruments Dallas fab (DFAB)		
Supplier Code:		Supplier Die Revision:	С		
Supplier Part Number:	SN104605PN	Supplier Assembly/Test Site:	Texas Instruments, Taiwan		
Customer Name:		Supplier Package / Pin:	PN/ 80		
Customer Part Number:		Pb-Free Lead Frame (Y/N):	Y		

Device Description:			"Green" Mold Compound (Y/N): Y						
MSL Rating: Level1			Operating Temp Range:			-40C to +125C			
Peak Solder Reflow Temp: 2		w Temp:	220C	Automotive Grade Level (1):			1		
Test	#	Reference	Test Conditions	Min Lots (2)	SS / lot (2)	Min Total (2)	Results Lot/pas s/fail	Comments: (N/A =Not Applicable)	Exceptions to AEC -Q100

TEST GROUP A – ACCELERATED ENVIRONMENT STRESS TESTS (3)

PC	A1	JESD22-113 J-STD-020	Preconditioning: SMD only; Moisture Preconditioning for THB/HAST, AC/UHST, TC, HTSL, and HTOL	Performed on <u>ALL</u> SMD devices prior to THB/HAST, AC/UHST, TC and PTC					
THB or HAST	A2	JESD22-A101 JESD22-A110	Temperature Humidity Bias: 85°C/85%/1000 hours Highly Accelerated Stress Test: 130°C/85%/96 hours or 110°C/85%/264 hours	3	77	231	3/231/ 0		
AC or UHST	A3	JESD22-A102 JESD22-A118	Autoclave: 121°C/15 psig/96 hours Unbiased Highly Accelerated Stress Test: 130°C/85%/96 hours or 110°C/85%/264 hours	3	77	231	3/231/ 0	QBS to existing 80PN package data	
ТС	A4	JESD22-A104	Temperature Cycle: -65°C/+150°C/500 cycles Post Temperature Cycle Bond Pull: 3 grams minimum	3	77 5	231 5	3/231/ 0 1/5/0	QBS to existing 80PN package data	

	TEST GROUP B – ACCELERATED LIFETIME SIMULATION TESTS (3)								
HTOL	B1	JESD22-A108	High Temp Operating Life: 125°C/1000 hours 150°C/408 hours	3	77	231	3/348/0		
ELFR	B2	AEC-Q100-008	Early Life Failure Rate:	3	800	2400	1/800/0	QBS to MAX32431 PWG4DL	One lot of ELFR.

	TEST GROUP C – PACKAGE ASSEMBLY INTEGRITY TESTS (3)								
WBS	C1	AEC-Q100-001	Wire Bond Shear Test:	20 bonds	5 parts	30	Pass		
			(Cpk > 1.67)	SO DOTIUS	min.	bonds	PdSS		
WBP	C2	Mil-Std-883	Wire Bond Pull:	30 bonds	5 parts	30	Pass		
		Method 2011	Each bonder used (Cpk > 1.67)	50 001103	min.	bonds	1 8 3 3		
SD	C3	JESD22-B102	Solderability: (>95% coverage) 8 hr steam age (1 hour for Au-plated leads)	1	30	30	1/30/0	QBS to existing 80PN package data	
PD	C4	JESD22-B100 JESD22-B108	Physical Dimensions: (Cpk > 1.67)	3	10	30	3/10/0	QBS to existing 80PN package data	

			TEST GROUP E- ELECTRICA	L VERIFIC	CATION				
TEST	E1	User/Supplier Specification	Pre and Post Stress Electrical Test:	All	All	All	Pass		
НВМ	E2	AEC-Q100-002	Electrostatic Discharge, Human Body Model: (2kV - H2 or better)	1	See Test Method			QBS to SN75976A2 DL	
MM	E2	AEC-Q100-003	Electrostatic Discharge, Machine Model: (200V – M3 or better)	1	See Test Method			QBS to SN75976A2 DL	
CDM	E3	AEC-Q100-101	Electrostatic Discharge, Charged Device Model: (750V corner leads, 500V for all other pins)	1	See Test Method		Pass	QBS to SN75976A2 DL	
LU	E4	AEC-Q100-004	Latch-Up:	1	6	6		QBS to SN75976A2 DL	
ED	E5	AEC-Q100-009	Electrical Distributions: (Cpk > 1.67)	1	30	30	Pass		

- (1) Grade 0 (or A): -40° C to $+150^{\circ}$ C ambient operating temperature range
 - Grade 1 (or Q): -40°C to +125°C ambient operating temperature range
 - Grade 2 (or T): -40°C to +105°C ambient operating temperature range
 - Grade 3 (or I): -40° C to $+85^{\circ}$ C ambient operating temperature range
 - Grade 4 (or C): -0°C to +150°C ambient operating temperature range
- (2) These are recommended minimum lot/sample sizes. Lot/sample size may be reduced depending on available data.
- (3) Generic data may be used.

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com